

EPC's Development Board Demonstrates Ease of Designing

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[Efficient Power Conversion Corporation](http://www.epc-co.com)

[EPC](http://www.epc-co.com) [1] (El Segundo, CA) has announced the availability of the EPC9004 development board, featuring EPC's enhancement-mode gallium nitride (eGaN) field effect transistors (FETs). This board demonstrates how recently introduced IC gate drivers, optimized for GaN FETs, make the task of transitioning from silicon power transistors to higher performance eGaN FETs simple and cost effective. Additional features include:

- A 200 V peak voltage.
- A max output current of 2 A.
- A half bridge featuring the EPC2012 eGaN FET.
- A dedicated gate driver, on a single 2" x 1.5" board.

For more information visit www.epc-co.com [1].

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http://www.wirelessdesignmag.com/product-releases/2013/02/epc%E2%80%99s-development-board-demonstrates-ease-designing?qt-most_popular=0&qt-digital_editions=0

Links:

[1] <http://www.epc-co.com>